

Thyristor Module

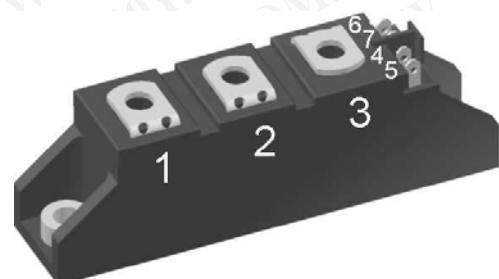
V_{RRM} = 2x 1600V
 I_{TAV} = 60A
 V_T = 1.24V

Phase leg

Part number

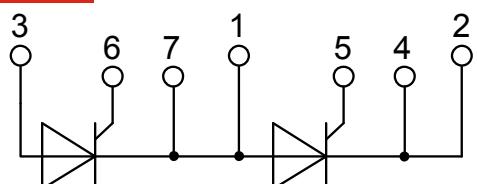
MCC56-16io1B

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)



Backside: isolated

E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

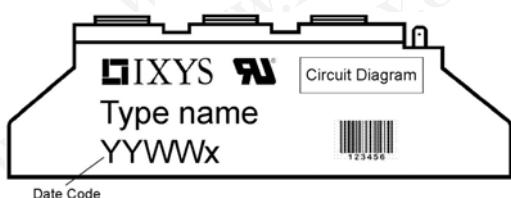
- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^\circ C$			1600	V
I_{RD}	reverse current, drain current	$V_{RD} = 1600 V$ $V_{RD} = 1600 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		200 5	μA mA
V_T	forward voltage drop	$I_T = 100 A$ $I_T = 200 A$ $I_T = 100 A$ $I_T = 200 A$	$T_{VJ} = 25^\circ C$ $T_{VJ} = 125^\circ C$		1.26 1.57 1.24 1.62	V V
I_{TAV}	average forward current	$T_C = 85^\circ C$	$T_{VJ} = 125^\circ C$		60	A
$I_{T(RMS)}$	RMS forward current	180° sine			100	A
V_{TO}	threshold voltage	r_T slope resistance } for power loss calculation only	$T_{VJ} = 125^\circ C$		0.85	V
	slope resistance				3.7	$m\Omega$
R_{thJC}	thermal resistance junction to case				0.45	K/W
R_{thCH}	thermal resistance case to heatsink			0.20		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ C$		222	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 125^\circ C$ $V_R = 0 V$		1.50 1.62 1.28 1.38	kA kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ C$ $V_R = 0 V$ $T_{VJ} = 125^\circ C$ $V_R = 0 V$		11.3 10.9 8.13 7.87	kA^2s kA^2s kA^2s kA^2s
C_J	junction capacitance	$V_R = 400 V$ $f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ C$		74	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$ $t_p = 300 \mu s$	$T_C = 125^\circ C$		10 5 0.5	W W W
P_{GAV}	average gate power dissipation					
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^\circ C; f = 50 \text{ Hz}$ repetitive, $I_T = 150 A$ $t_p = 200 \mu s; di_G/dt = 0.45 A/\mu s;$ $I_G = 0.45 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 60 A$			150	$A/\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 125^\circ C$		1000	$V/\mu s$
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		1.5 1.6	V V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$		100 200	mA mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^\circ C$		0.2	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 10 \mu s$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		450	mA
I_H	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ C$		200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$	$T_{VJ} = 25^\circ C$		2	μs
t_q	turn-off time	$V_R = 100 V; I_T = 150 A; V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^\circ C$ $di/dt = 10 A/\mu s; dv/dt = 20 V/\mu s; t_p = 200 \mu s$		150		μs

Package TO-240AA			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			200	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		125	°C
Weight				90		g
M_D	mounting torque		2.5		4	Nm
M_T	terminal torque		2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
V_{ISOL}	isolation voltage	t = 1 second t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600 3000			V V



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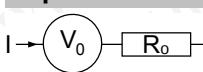
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCC56-16io1B	MCC56-16io1B	Box	6	452769

Similar Part	Package	Voltage class
MCMA65P1600TA	TO-240AA-1B	1600
MCMA85P1600TA	TO-240AA-1B	1600

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 125^\circ\text{C}$



Thyristor

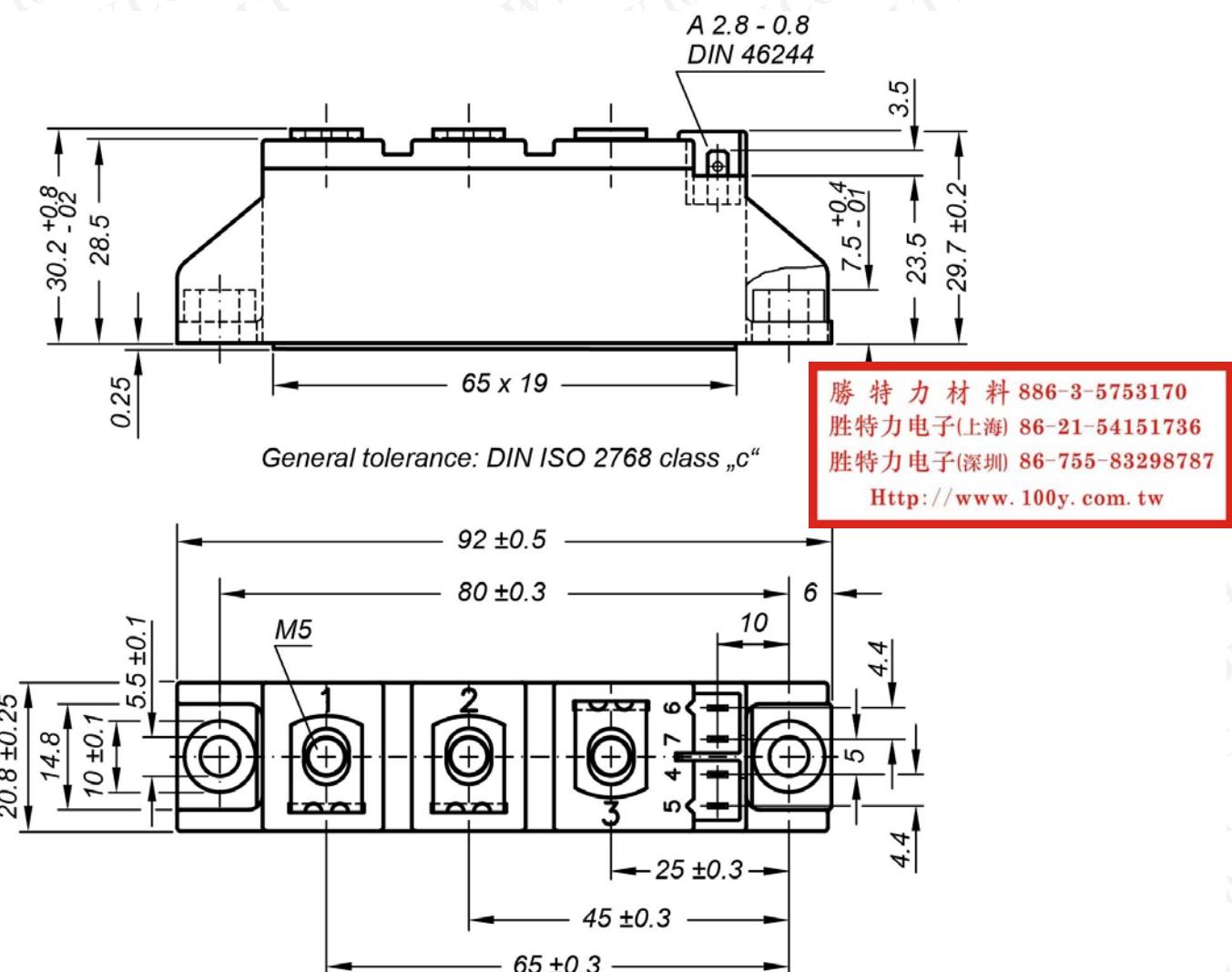
$V_{0\max}$ threshold voltage 0.85

$R_{0\max}$ slope resistance * 2.5

V

mΩ

Outlines TO-240AA



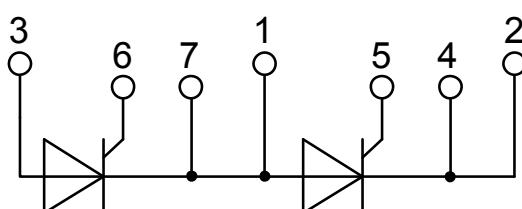
Optional accessories: Keyed gate/cathode twin plugs

Wire length: 350 mm, gate = white, cathode = red

UL 758, style 3751

Type ZY 200L (L = Left for pin pair 4/5)

Type ZY 200R (R = Right for pin pair 6/7)



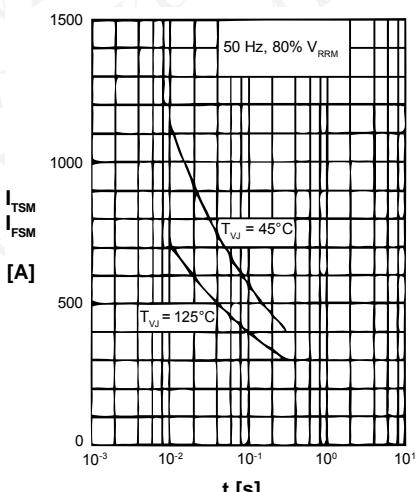
Thyristor

Fig. 1 Surge overload current
 I_{TSM}, I_{FSM} : Crest value, t: duration

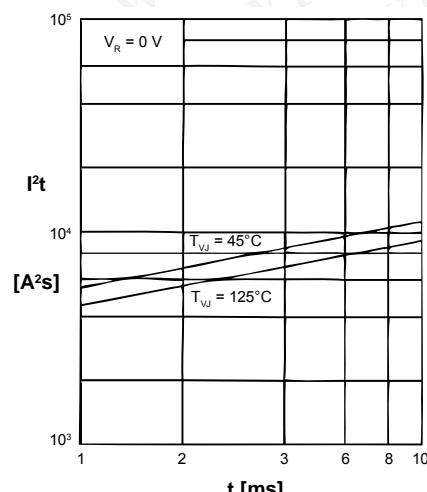


Fig. 2 I^2t versus time (1-10 ms)

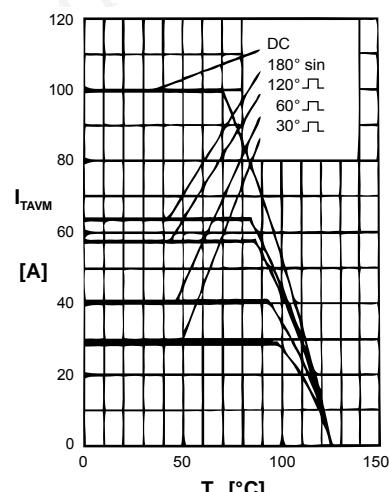


Fig. 3 Maximum forward current
at case temperature

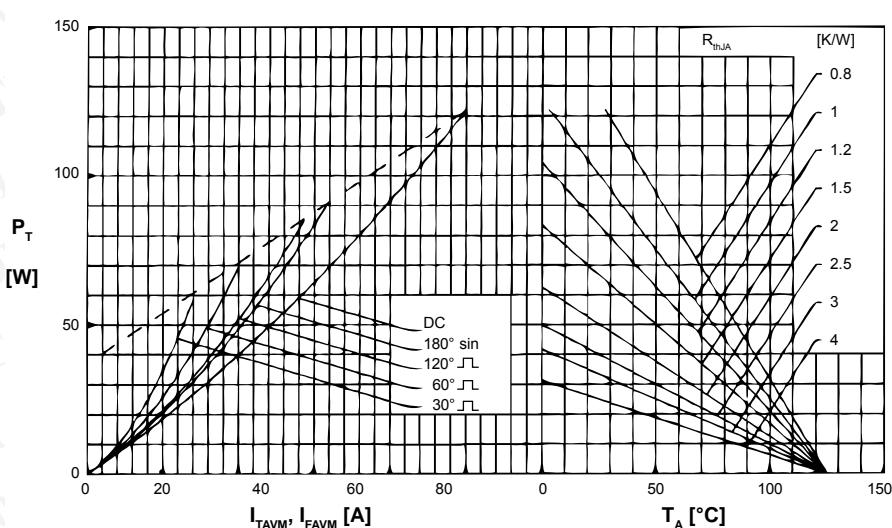


Fig. 4 Power dissipation vs. onstate current and ambient temperature (per thyristor/diode)

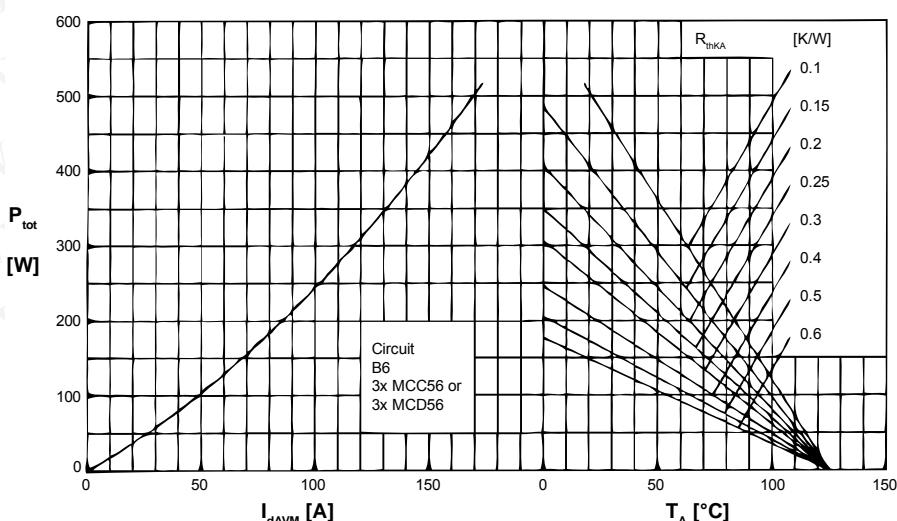


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current
and ambient temperature

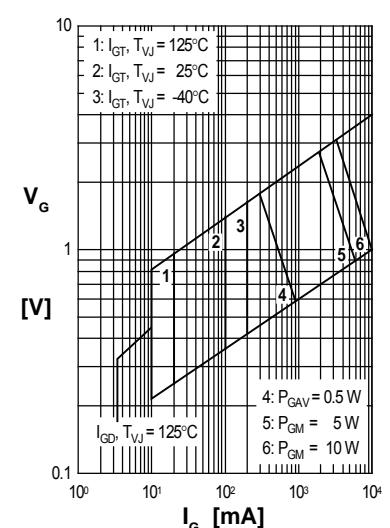


Fig. 5 Gate trigger charact.

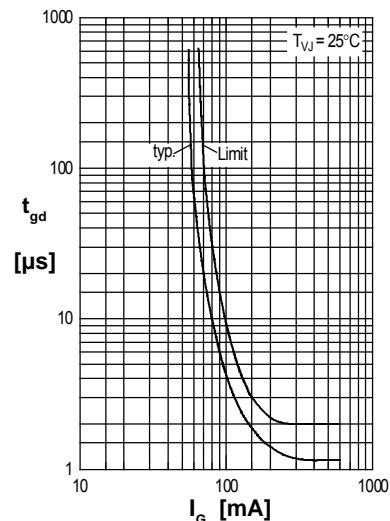


Fig. 7 Gate trigger delay time

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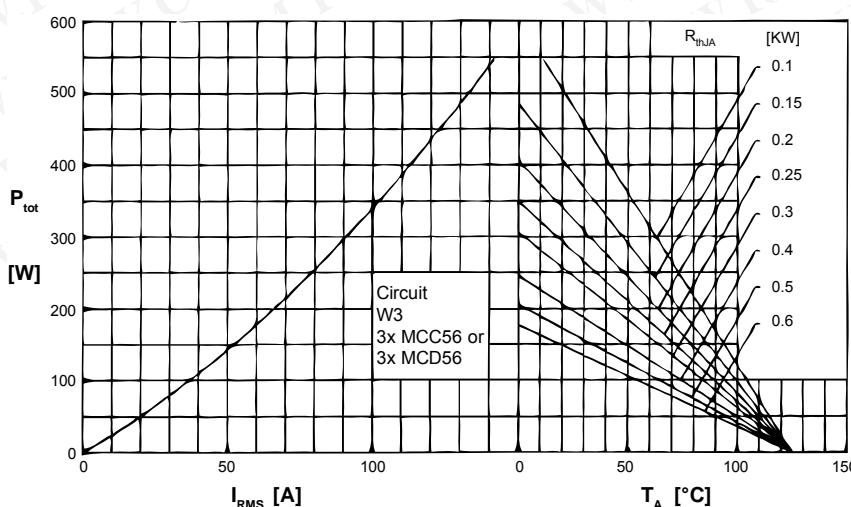


Fig. 8 Three phase AC-controller: Power dissipation vs. RMS output current and ambient temperature

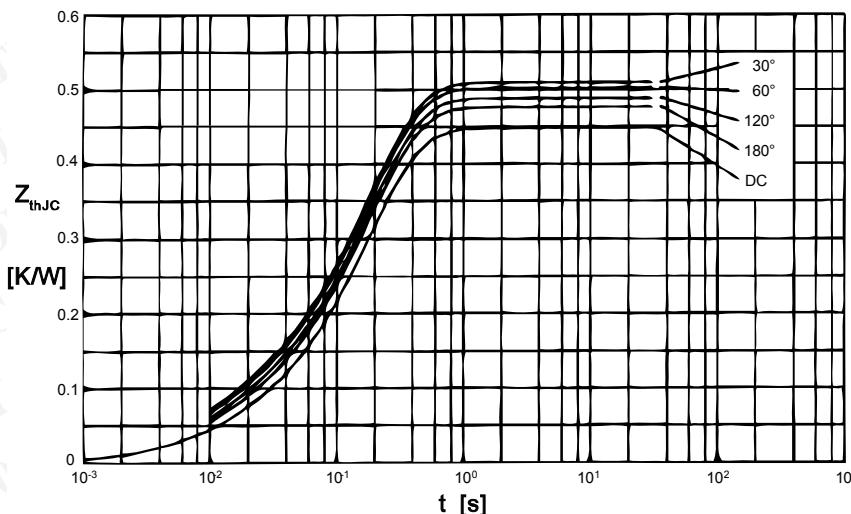


Fig. 9 Transient thermal impedance junction to case (per thyristor)

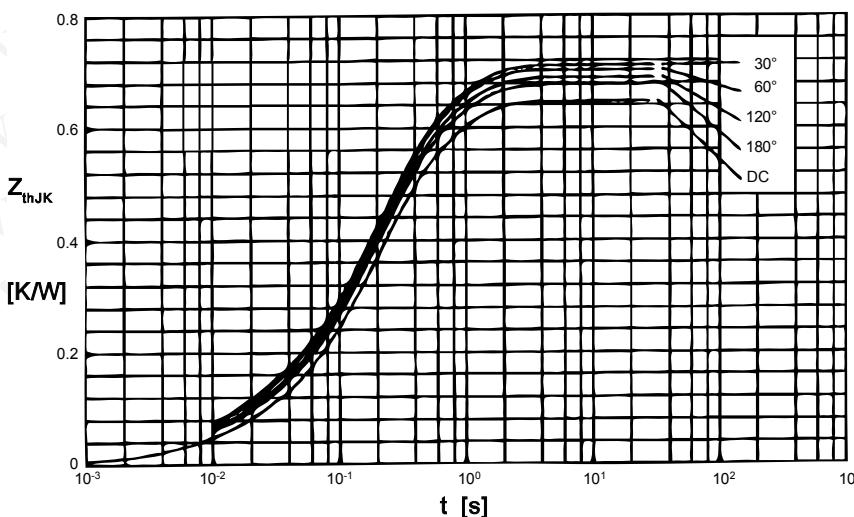


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

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R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.450
180°	0.470
120°	0.490
60°	0.505
30°	0.520

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.650
180°	0.670
120°	0.690
60°	0.705
30°	0.720

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.014	0.0150
2	0.026	0.0095
3	0.410	0.1750
4	0.200	0.6700